

2SA1585 PNP Silicon Epitaxial Planar Transistor

The transistor is subdivided into two groups, Q and R, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	20	V
Collector Emitter Voltage	$-V_{CEO}$	20	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current	$-I_C$ $-I_{CP}^{1)}$	2 5	A
Power Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

¹⁾ Single pulse $P_w = 10\text{ ms}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 2\text{ V}$, $-I_C = 100\text{ mA}$	Current Gain Group Q R	h_{FE} h_{FE}	120 180	- -	270 390	- -
Collector Base Breakdown Voltage at $-I_C = 50\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	20	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	20	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 50\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	-	V	
Collector Cutoff Current at $-V_{CB} = 20\text{ V}$	$-I_{CBO}$	-	-	100	nA	
Emitter Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	100	nA	
Collector Emitter Saturation Voltage at $-I_C = 2\text{ A}$, $-I_B = 0.1\text{ A}$	$-V_{CE(sat)}$	-	-	0.5	V	
Transition Frequency at $-V_{CE} = 2\text{ V}$, $I_E = 500\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	240	-	MHz	
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{OB}	-	35	-	pF	

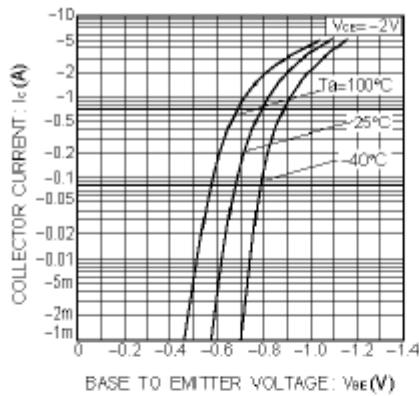


Fig.1 Grounded emitter propagation characteristics

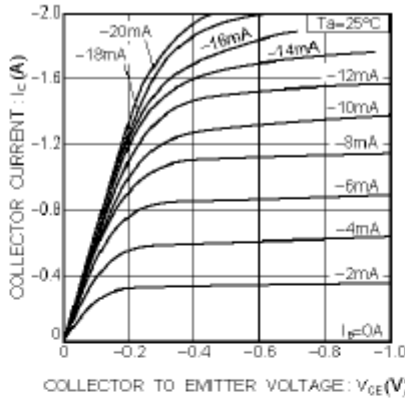


Fig.2 Grounded emitter output characteristics (I)

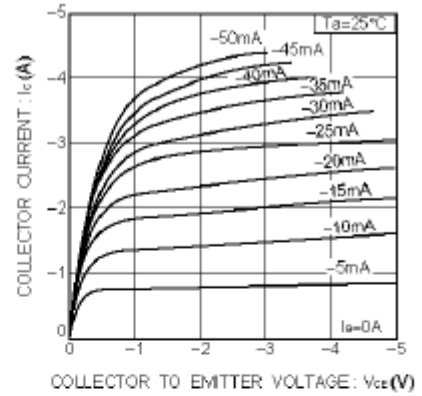


Fig.3 Grounded emitter output characteristics (II)

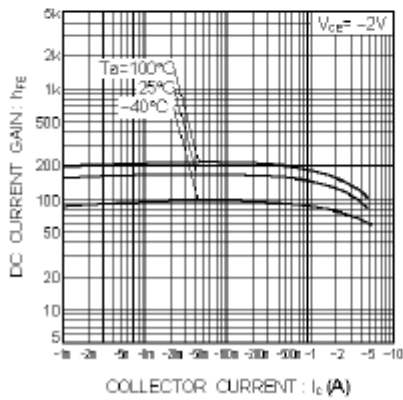


Fig.4 DC current gain vs. collector current

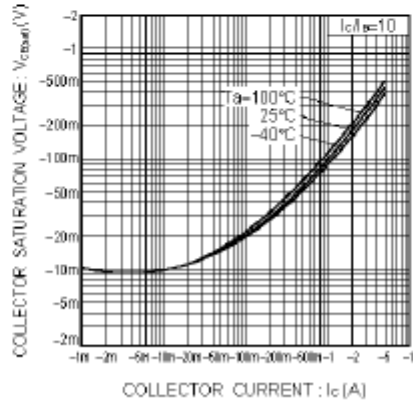


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

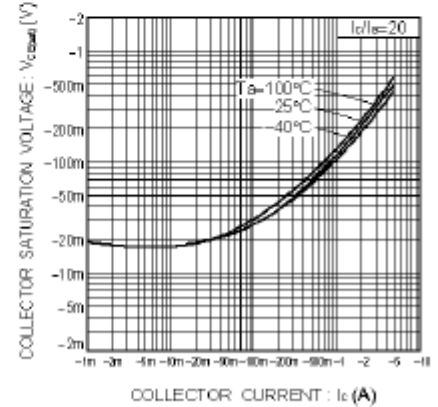


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

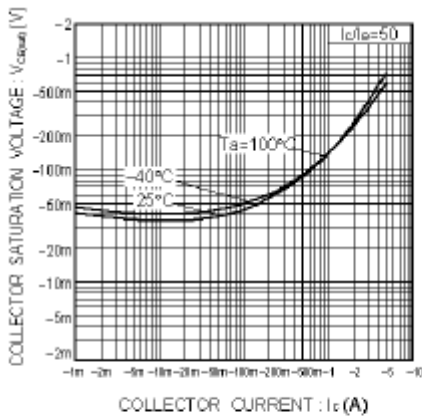


Fig.7 Collector-emitter saturation voltage vs. collector current (III)

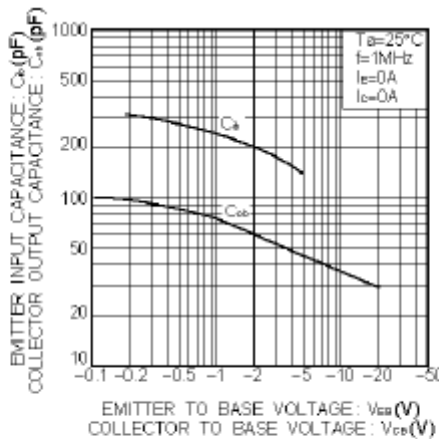


Fig.8 Gain bandwidth product vs. emitter current
Collector output capacitance vs. collector-base voltage

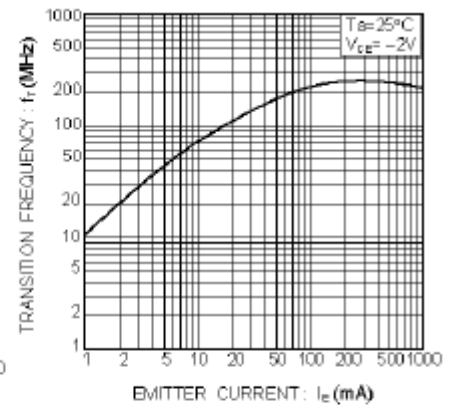


Fig.9 Emitter input capacitance vs. emitter base voltage